

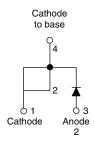
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# HEXFRED® Ultrafast Soft Recovery Diode, 25 A



TO-247AC modified



| PRODUCT SUMMAR                   | Υ                          |
|----------------------------------|----------------------------|
| Package                          | TO-247AC modified (2 pins) |
| I <sub>F(AV)</sub>               | 25 A                       |
| $V_{R}$                          | 600 V                      |
| V <sub>F</sub> at I <sub>F</sub> | 1.3 V                      |
| t <sub>rr</sub> (yp.             | 23 ns                      |
| T <sub>J</sub> max.              | 150 °C                     |
| Diode variation                  | Single die                 |

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





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### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- Reduced parts count

#### **DESCRIPTION**

VS-HFA25PB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25PB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25PB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

| ABSOLUTE MAXIMUM RATINGS                         |                                   |                         |             |       |  |  |
|--|-----------------------------------|-------------------------|-------------|-------|--|--|
| PARAMETER  | SYMBOL                            | TEST CONDITIONS         | VALUES      | UNITS |  |  |
| Cathode to anode voltage                         | $V_{R}$                           |                         | 600         | V     |  |  |
| Maximum continuous forward current               | I <sub>F</sub>                    | T <sub>C</sub> = 100 °C | 25          |       |  |  |
| Single pulse forward current                     | I <sub>FSM</sub>                  |                         | 225         | Α     |  |  |
| Maximum repetitive forward current               | I <sub>FRM</sub>                  |                         | 100         |       |  |  |
| Maximum nawar dissination                        | P <sub>D</sub>                    | T <sub>C</sub> = 25 °C  | 151         | W     |  |  |
| Maximum power dissipation                        |                                   | T <sub>C</sub> = 100 °C | 60          | ] vv  |  |  |
| Operating junction and storage temperature range | T <sub>J</sub> , T <sub>Stg</sub> |                         | -55 to +150 | °C    |  |  |



# VS-HFA25PB60PbF, VS-HFA25PB60-N3

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| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |   |  |            |      |      |       |    |
|--|---|--|------------|------|------|-------|----|
| PARAMETER  | SYMBOL  | TEST CONDITIONS                                | MIN.       | TYP. | MAX. | UNITS |    |
| Cathode to anode breakdown voltage   | V <sub>BR</sub>   | R I <sub>R</sub> = 100 μA                      |            | 600  | -    | -     |    |
| Maximum forward voltage  |   | I <sub>F</sub> = 25 A                          | See fig. 1 | -    | 1.3  | 1.7   | V  |
|  | $V_{FM}$  | I <sub>F</sub> = 50 A                          |            | -    | 1.5  | 2.0   |    |
|  |   | I <sub>F</sub> = 25 A, T <sub>J</sub> = 125 °C |            | -    | 1.3  | 1.7   |    |
| Maximum reverse  |   | V <sub>R</sub> = V <sub>R</sub> rated          | Soo fig. 2 | -    | 1.5  | 20    |    |
| leakage current  | $I_{RM}$ $T_J = 125 ^{\circ}\text{C}, V_R = 0.8 ^{\circ}\text{X} ^{\circ}\text{N}$ See fig. 2 |  | See lig. 2 | -    | 600  | 2000  | μΑ |
| Junction capacitance   | C <sub>T</sub>  | V <sub>R</sub> = 200 V                         | See fig. 3 | -    | 55   | 100   | pF |
| Series inductance  | L <sub>S</sub>  | Measured lead to lead 5 mm from package body   |            | -    | 12   | -     | nH |

| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                           |                                      |   |      |      |      |       |
|---|---------------------------|--------------------------------------|---|------|------|------|-------|
| PARAMETER   | SYMBOL                    | TEST CO                              | NDITIONS  | MIN. | TYP. | MAX. | UNITS |
|   | t <sub>rr</sub>           | $I_F = 1.0 \text{ A}, dI_F/dt = 200$ | A/μs, V <sub>R</sub> = 30 V   | -    | 23   | -    |       |
| Reverse recovery time See fig. 5, 10  | t <sub>rr1</sub>          | T <sub>J</sub> = 25 °C               |   | -    | 50   | 75   | ns    |
| Gee lig. 5, 10  | t <sub>rr2</sub>          | T <sub>J</sub> = 125 °C              | I <sub>F</sub> = 25 A<br>dI <sub>F</sub> /dt = 200 A/μs<br>V <sub>R</sub> = 200 V | =    | 105  | 160  |       |
| Peak recovery current   | I <sub>RRM1</sub>         | T <sub>J</sub> = 25 °C               |   | =    | 4.5  | 10   | A nC  |
| See fig. 6, 10  | I <sub>RRM2</sub>         | T <sub>J</sub> = 125 °C              |   | -    | 8.0  | 15   |       |
| Reverse recovery charge   | Q <sub>rr1</sub>          | T <sub>J</sub> = 25 °C               |   | -    | 112  | 375  |       |
| See fig. 7, 10  | Q <sub>rr2</sub>          | T <sub>J</sub> = 125 °C              |   | =    | 420  | 1200 | nc    |
| Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8, 10                  | dI <sub>(rec)M</sub> /dt1 | T <sub>J</sub> = 25 °C               |   | -    | 250  | -    | A/µs  |
|   | dI <sub>(rec)M</sub> /dt2 | T <sub>J</sub> = 125 °C              |   | -    | 160  | -    | AνμS  |

| THERMAL - MECHANICAL SPECIFICATIONS     |                   |  |              |      |            |                      |
|---|-------------------|--|--------------|------|------------|----------------------|
| PARAMETER                               | SYMBOL            | TEST CONDITIONS                            | MIN.         | TYP. | MAX.       | UNITS                |
| Lead temperature                        | T <sub>lead</sub> | 0.063" from case (1.6 mm) for 10 s         | -            | -    | 300        | °C                   |
| Thermal resistance, junction to case    | R <sub>thJC</sub> |  | -            | -    | 0.83       |                      |
| Thermal resistance, junction to ambient | R <sub>thJA</sub> | Typical socket mount                       | -            | -    | 40         | K/W                  |
| Thermal resistance, case to heatsink    | R <sub>thCS</sub> | Mounting surface, flat, smooth and greased | -            | 0.25 | -          |                      |
| Weight                                  |                   |  | -            | 6.0  | -          | g                    |
| vveignit                                |                   |  | -            | 0.21 | -          | OZ.                  |
| Mounting torque                         |                   |  | 6.0<br>(5.0) | -    | 12<br>(10) | kgf ·cm<br>(lbf ·in) |
| Marking device                          |                   | Case style TO-247AC modified (JEDEC)       | HFA25PB60    |      |            |                      |

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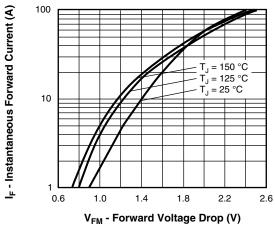


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

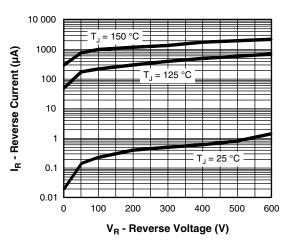


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

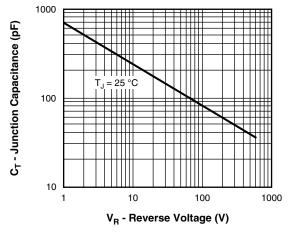


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

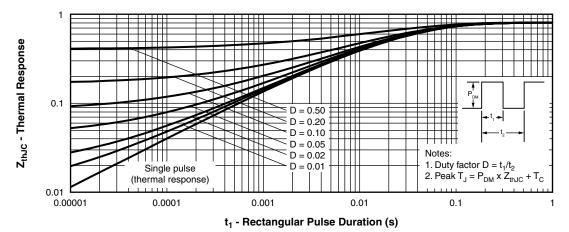


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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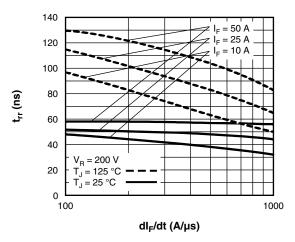


Fig. 5 - Typical Reverse Recovery Time vs. dI<sub>E</sub>/dt

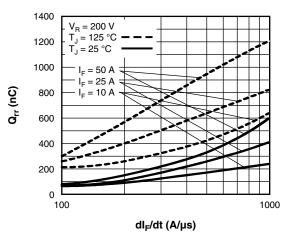


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

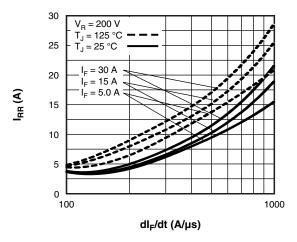


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

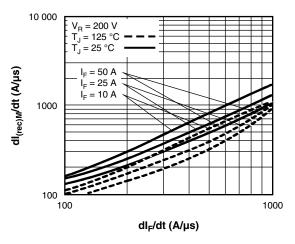


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt

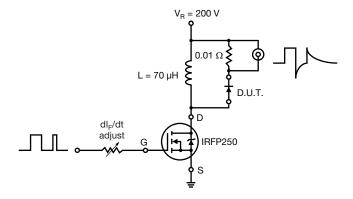
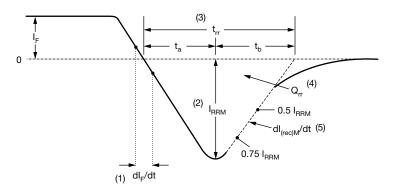


Fig. 9 - Reverse Recovery Parameter Test Circuit

# VS-HFA25PB60PbF, VS-HFA25PB60-N3

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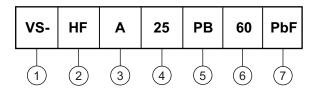


- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (2) I<sub>RRM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (5) dl<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

### Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- Electron irradiated
- 4 Current rating (25 = 25 A)
- PB = TO-247AC modified
- Voltage rating: (60 = 600 V)
- 7 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

| ORDERING INFORMATION (Example) |                  |                        |                         |  |  |  |  |
|--------------------------------|------------------|------------------------|-------------------------|--|--|--|--|
| PREFERRED P/N                  | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION   |  |  |  |  |
| VS-HFA25PB60PbF                | 25               | 500                    | Antistatic plastic tube |  |  |  |  |
| VS-HFA25PB60-N3                | 25               | 500                    | Antistatic plastic tube |  |  |  |  |

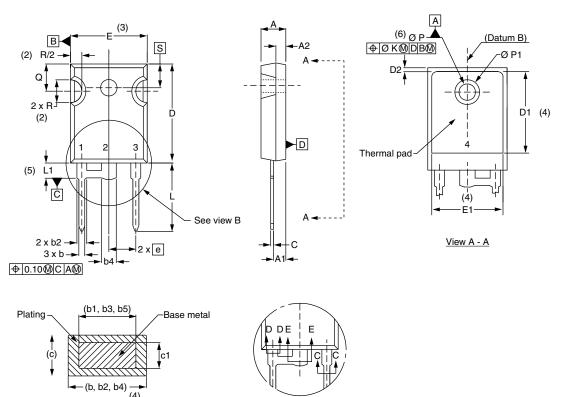
| LINKS TO RELATED DOCUMENTS |                       |                          |  |  |  |  |
|----------------------------|-----------------------|--------------------------|--|--|--|--|
| Dimensions                 |                       | www.vishay.com/doc?95541 |  |  |  |  |
| Dort marking information   | TO-247AC modified PbF | www.vishay.com/doc?95255 |  |  |  |  |
| Part marking information   | TO-247AC modified -N3 | www.vishay.com/doc?95442 |  |  |  |  |



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### TO-247AC modified - 50 mils L/F

### **DIMENSIONS** in millimeters and inches



View B

| SYMBOL  | MILLIM | MILLIMETERS |       | INCHES |       |
|---------|--------|-------------|-------|--------|-------|
| STWIBOL | MIN.   | MAX.        | MIN.  | MAX.   | NOTES |
| Α       | 4.65   | 5.31        | 0.183 | 0.209  |       |
| A1      | 2.21   | 2.59        | 0.087 | 0.102  |       |
| A2      | 1.17   | 1.37        | 0.046 | 0.054  |       |
| b       | 0.99   | 1.40        | 0.039 | 0.055  |       |
| b1      | 0.99   | 1.35        | 0.039 | 0.053  |       |
| b2      | 1.65   | 2.39        | 0.065 | 0.094  |       |
| b3      | 1.65   | 2.34        | 0.065 | 0.092  |       |
| b4      | 2.59   | 3.43        | 0.102 | 0.135  |       |
| b5      | 2.59   | 3.38        | 0.102 | 0.133  |       |
| С       | 0.38   | 0.89        | 0.015 | 0.035  |       |
| c1      | 0.38   | 0.84        | 0.015 | 0.033  |       |
| D       | 19.71  | 20.70       | 0.776 | 0.815  | 3     |
| D1      | 13.08  | -           | 0.515 | -      | 4     |

Section C - C, D - D, E - E

| SYMBOL  | MILLIM   | IETERS | INC       | HES   | NOTES |
|---------|----------|--------|-----------|-------|-------|
| STWIDOL | MIN.     | MAX.   | MIN.      | MAX.  | NOTES |
| D2      | 0.51     | 1.35   | 0.020     | 0.053 |       |
| E       | 15.29    | 15.87  | 0.602     | 0.625 | 3     |
| E1      | 13.46    | -      | 0.53      | -     |       |
| е       | 5.46 BSC |        | 0.215     | BSC   |       |
| ØK      | 0.254    |        | 0.010     |       |       |
| L       | 14.20    | 16.10  | 0.559     | 0.634 |       |
| L1      | 3.71     | 4.29   | 0.146     | 0.169 |       |
| ØΡ      | 3.56     | 3.66   | 0.14      | 0.144 |       |
| Ø P1    | -        | 7.39   | -         | 0.291 |       |
| Q       | 5.31     | 5.69   | 0.209     | 0.224 |       |
| R       | 4.52     | 5.49   | 0.178     | 0.216 |       |
| S       | 5.51 BSC |        | 0.217 BSC |       |       |
|         |          |        |           |       |       |

#### Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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